

### Vishay High Power Products

# Thyristor/Thyristor, 150 A (New INT-A-PAK Power Module)



**New INT-A-PAK** 

| PRODUCT SUMMARY    |       |
|--------------------|-------|
| I <sub>T(AV)</sub> | 150 A |

### **FEATURES**

- Electrically isolated by DBC ceramic (Al<sub>2</sub>O<sub>3</sub>)
- 3500 V<sub>RMS</sub> isolating voltage
- Industrial standard package
- High surge capability
- · Glass passivated chips
- Simple mounting
- UL approved file E78996 **T**
- Compliant to RoHS directive 2002/95/EC
- Designed and qualified for multiple level

### **APPLICATIONS**

- · Battery charges
- Welders
- Power converters

| MAJOR RATINGS AND CHARACTERISTICS |                 |             |                     |  |  |  |  |  |
|-----------------------------------|-----------------|-------------|---------------------|--|--|--|--|--|
| SYMBOL                            | CHARACTERISTICS | VALUES      | UNITS               |  |  |  |  |  |
| I <sub>T(AV)</sub>                | 85 °C           | 150         | A                   |  |  |  |  |  |
| I <sub>T(RMS)</sub>               |                 | 330         |                     |  |  |  |  |  |
|                                   | 50 Hz           | 4000        | Α                   |  |  |  |  |  |
| I <sub>TSM</sub>                  | 60 Hz           | 4200        |                     |  |  |  |  |  |
| l <sup>2</sup> t                  | 50 Hz           | 50 Hz 80    |                     |  |  |  |  |  |
| 1-1                               | 60 Hz           | 73          | - kA <sup>2</sup> s |  |  |  |  |  |
| l²√t                              |                 | 800         | kA²√s               |  |  |  |  |  |
| V <sub>RRM</sub>                  |                 | 400         | V                   |  |  |  |  |  |
| T <sub>Stg</sub>                  | Range           | - 40 to 150 | °C                  |  |  |  |  |  |
| $T_J$                             | Range           | - 40 to 125 | O                   |  |  |  |  |  |

#### **ELECTRICAL SPECIFICATIONS**

| VOLTAGE RATINGS |  |  |   |  |  |  |  |  |
|-----------------|--|--|---|--|--|--|--|--|
| TYPE NUMBER     | V <sub>RRM</sub> /V <sub>DRM</sub> , MAXIMUM REPETITIVE<br>PEAK REVERSE VOLTAGE<br>V | V <sub>RSM</sub> /V <sub>DSM</sub> , MAXIMUM NON-REPETITIVE<br>PEAK REVERSE VOLTAGE<br>V | I <sub>RRM</sub> /I <sub>DRM</sub><br>AT 125 °C<br>mA |  |  |  |  |  |
| VSKT152/04PbF   | 400  | 500  | 50  |  |  |  |  |  |

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### VSKT152/04PbF



# Vishay High Power Products Thyristor/Thyristor, 150 A (New INT-A-PAK Power Module)

| ON-STATE CONDUCTION                              |                     |   |                        |   |        |                    |
|--|---------------------|---|------------------------|---|--------|--------------------|
| PARAMETER  | SYMBOL              | TEST CONDITIONS   |                        |   | VALUES | UNITS              |
| Maximum average on-state current                 | I <sub>T(AV)</sub>  | 180° conductio  | on half sine wave      |   | 150    | Α                  |
| at case temperature                              | 1(11)               |   |                        |   | 85     | °C                 |
| Maximum RMS on-state current                     | I <sub>T(RMS)</sub> | As AC switch  |                        |   | 330    |                    |
|  |                     | t = 10 ms   | No voltage             |   | 4000   |                    |
| Maximum peak, one-cycle on-state, non-repetitive |                     | t = 8.3 ms  | reapplied              | Sine half wave,<br>initial T <sub>J</sub> =<br>T <sub>J</sub> maximum | 4200   | Α                  |
| surge current                                    | I <sub>TSM</sub>    | t = 10 ms   | 100 % V <sub>RRM</sub> |   | 3350   |                    |
|  |                     | t = 8.3 ms  | reapplied              |   | 3500   |                    |
|  | l <sup>2</sup> t    | t = 10 ms   | No voltage reapplied   |   | 80     | kA <sup>2</sup> s  |
|  |                     | t = 8.3 ms  |                        |   | 73     |                    |
| Maximum I <sup>2</sup> t for fusing              |                     | t = 10 ms   | 100 % V <sub>RRM</sub> |   | 56     |                    |
|  |                     | t = 8.3 ms  | reapplied              |   | 51     |                    |
| Maximum I <sup>2</sup> √t for fusing             | I²√t                | t = 0.1 ms to 10  | 0 ms, no voltage r     | eapplied  | 800    | kA <sup>2√</sup> s |
| Value of threshold voltage                       | V <sub>T(TO)</sub>  | T. ma avrima uma  |                        |   | 0.82   | V                  |
| On-state slope resistance                        | r <sub>t</sub>      | T <sub>J</sub> maximum  |                        | 1.44  | mΩ     |                    |
| Maximum on-state voltage drop                    | $V_{TM}$            | $I_{pk} = \pi \times I_{T(AV)}, T_J = 25 ^{\circ}C$                           |                        |   | 1.48   | V                  |
| Maximum holding current                          | I <sub>H</sub>      | T <sub>J</sub> = 25 °C, anode supply = 6 V, resistive load, gate open circuit |                        |   | 200    | mA                 |
| Maximum latching current                         | ΙL                  | $T_J = 25$ °C, and  | ode supply = 6 V,      | resistive load  | 400    |                    |

| SWITCHING             |                 |  |  |           |       |
|-----------------------|-----------------|--|--|-----------|-------|
| PARAMETER             | SYMBOL          |  | TEST CONDITIONS                                  | VALUES    | UNITS |
| Typical delay time    | t <sub>gd</sub> | T <sub>.1</sub> = 25 °C  | Gate current = 1 A, dl <sub>g</sub> /dt = 1 A/µs | 1         |       |
| Typical rise time     | t <sub>gr</sub> | 1j = 25 C  | $V_{d} = 0.67 \% V_{DRM}$                        | 2         | μs    |
| Typical turn-off time | tq              | $I_{TM}$ = 300 A, - dl/dt = 15 A/μs; $T_J$ = $T_J$ maximum $V_R$ = 50 V; dV/dt = 20 V/μs; gate 0 V, 100 $\Omega$ |  | 50 to 200 | ·     |

| BLOCKING   |                                       |  |        |       |  |  |  |  |  |
|--|---------------------------------------|--|--------|-------|--|--|--|--|--|
| PARAMETER  | SYMBOL                                | TEST CONDITIONS  | VALUES | UNITS |  |  |  |  |  |
| Maximum peak reverse and off-state leakage current | I <sub>RRM,</sub><br>I <sub>DRM</sub> | T <sub>J</sub> = 125 °C                                  | 50     | mA    |  |  |  |  |  |
| RMS insulation voltage                             | V <sub>INS</sub>                      | 50 Hz, circuit to base, all terminals shorted, t = 1 s   | 3500   | V     |  |  |  |  |  |
| Critical rate of rise of off-state voltage         | dV/dt                                 | $T_J = T_J$ maximum, exponential to 67 % rated $V_{DRM}$ | 1000   | V/µs  |  |  |  |  |  |

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## Thyristor/Thyristor, 150 A Vishay High Power Products (New INT-A-PAK Power Module)

| TRIGGERING                                  |                    |   |                                      |                                    |       |  |
|---|--------------------|---|--------------------------------------|------------------------------------|-------|--|
| PARAMETER                                   | SYMBOL             | TEST CON  | IDITIONS                             | VALUES                             | UNITS |  |
| Maximum peak gate power                     | P <sub>GM</sub>    | $t_p \le 5 \text{ ms}, T_J = T_J \text{ maxim}$ | num                                  | 12                                 | W     |  |
| Maximum average gate power                  | P <sub>G(AV)</sub> | $f = 50 \text{ Hz}, T_J = T_J \text{ maxim}$    | ium                                  | 3                                  | VV    |  |
| Maximum peak gate current                   | I <sub>GM</sub>    |   |                                      | 3                                  | Α     |  |
| Maximum peak negative gate voltage          | - V <sub>GT</sub>  | $t_p \le 5$ ms, $T_J = T_J$ maxim               | num                                  | 10                                 |       |  |
|   |                    | T <sub>J</sub> = - 40 °C                        |                                      | 4                                  | V     |  |
| Maximum required DC gate voltage to trigger | $V_{GT}$           | T <sub>J</sub> = 25 °C                          |                                      | 2.5                                |       |  |
| voltage to trigger                          |                    | $T_J = T_J$ maximum                             | Anode supply = 6 V,                  | 1.7                                |       |  |
|   |                    | T <sub>J</sub> = - 40 °C                        | resistive load; $R_a = 1 \Omega$     | sistive load; $R_a = 1 \Omega$ 270 |       |  |
| Maximum required DC gate current to trigger | I <sub>GT</sub>    | T <sub>J</sub> = 25 °C                          |                                      | 150                                | mA    |  |
| current to trigger                          |                    | $T_J = T_J$ maximum                             |                                      | 80                                 |       |  |
| Maximum gate voltage that will not trigger  | $V_{GD}$           | T. T. manyimayan watad                          | V applied                            | 0.3                                | V     |  |
| Maximum gate current that will not trigger  | I <sub>GD</sub>    | $T_J = T_J$ maximum, rated                      | v <sub>DRM</sub> applied             | 10                                 | mA    |  |
| Maximum rate of rise of turned-on current   | dl/dt              | $T_J = T_J$ maximum, $I_{TM} = 4$               | 400 A rated V <sub>DRM</sub> applied | 300                                | A/µs  |  |

| THERMAL AND MECHANICAL SPECIFICATIONS                     |                   |  |             |        |  |  |  |
|---|-------------------|--|-------------|--------|--|--|--|
| PARAMETER   | SYMBOL            | TEST CONDITIONS                                  | VALUES      | UNITS  |  |  |  |
| Maximum junction operating temperature range              | TJ                |  | - 40 to 125 | °C     |  |  |  |
| Maximum storage temperature range                         | T <sub>Stg</sub>  |  | - 40 to 150 | C      |  |  |  |
| Maximum thermal resistance, junction to case per junction | R <sub>thJC</sub> | DC operation                                     | 0.18        | K/W    |  |  |  |
| Maximum thermal resistance, case to heatsink per module   |                   | Mounting surface smooth, flat and greased        | 0.05        | FC/ VV |  |  |  |
| Mounting IAP to heatsink                                  |                   | A mounting compound is recommended and           | 4 to 6      | Nime   |  |  |  |
| torque ± 10 % busbar to IAP                               |                   | the torque should be rechecked after a period of | 4 10 6      | Nm     |  |  |  |
| Approximate weight  |                   | 3 hours to allow for the spread of the compound. | 200         | g      |  |  |  |
| Approximate weight  |                   | Lubricated threads.                              | 7.1         | OZ.    |  |  |  |
| Case style  |                   |  | New INT-    | A-PAK  |  |  |  |

| △R CONDUCTION PER JUNCTION |  |       |       |       |       |       |       |       |       |       |     |
|----------------------------|--|-------|-------|-------|-------|-------|-------|-------|-------|-------|-----|
| DEVICES                    | SINUSOIDAL CONDUCTION AT T <sub>J</sub> MAXIMUM RECTANGULAR CONDUCTION AT T <sub>J</sub> MAXIMUM |       |       |       |       |       |       | UNITS |       |       |     |
|                            | 180°   | 120°  | 90°   | 60°   | 30°   | 180°  | 120°  | 90°   | 60°   | 30°   |     |
| VSKT152/04PbF              | 0.007  | 0.010 | 0.013 | 0.016 | 0.017 | 0.009 | 0.012 | 0.014 | 0.016 | 0.017 | K/W |

#### Note

• Table shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

## Vishay High Power Products Thyristor/Thyristor, 150 A (New INT-A-PAK Power Module)



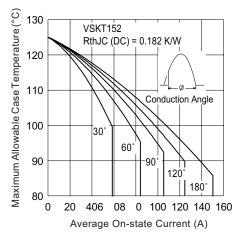


Fig. 1 - Current Ratings Characteristics

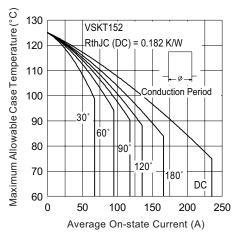


Fig. 2 - Current Ratings Characteristics

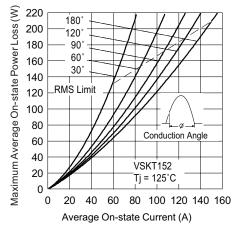


Fig. 3 - Forward Power Loss Characteristics

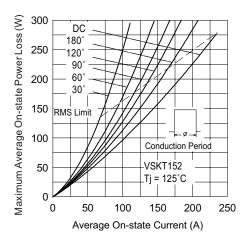


Fig. 4 - Forward Power Loss Characteristics

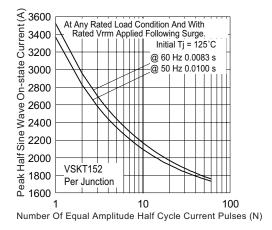


Fig. 5 - Maximum Non-Repetitive Surge Current

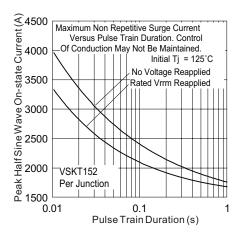


Fig. 6 - Maximum Non-Repetitive Surge Current



### Thyristor/Thyristor, 150 A Vishay High Power Products (New INT-A-PAK Power Module)

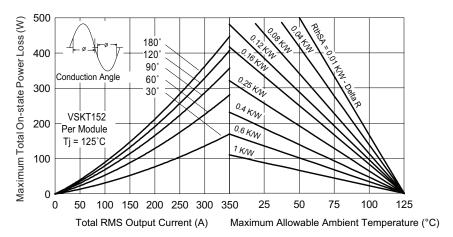


Fig. 7 - On-State Power Loss Characteristics

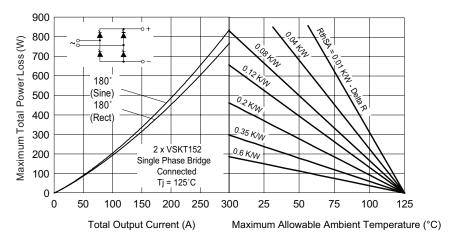


Fig. 8 - On-State Power Loss Characteristics

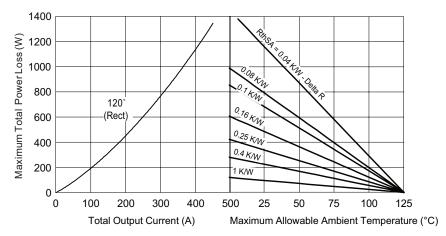


Fig. 9 - On-State Power Loss Characteristics

## Vishay High Power Products Thyristor/Thyristor, 150 A (New INT-A-PAK Power Module)



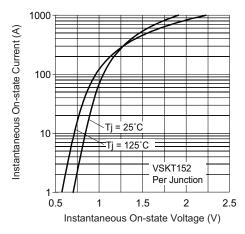


Fig. 10 - On-State Voltage Drop Characteristics

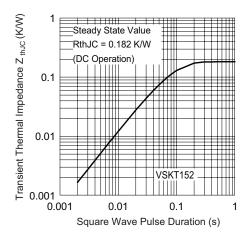


Fig. 11 - Thermal Impedance  $Z_{thJC}$  Characteristics

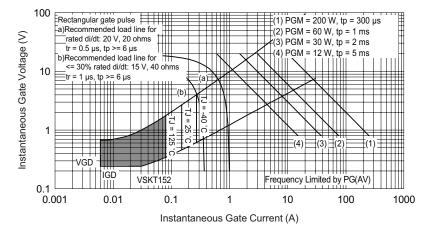


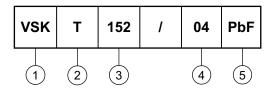
Fig. 12 - Gate Characteristics



Thyristor/Thyristor, 150 A Vishay High Power Products (New INT-A-PAK Power Module)

### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Module type

2 - Circuit configuration:

T = Two SCR doubler configuration

3 - Current rating

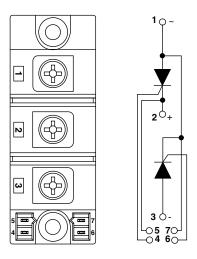
4 - Voltage rating (04 = 400 V)

5 - PbF = Lead (Pb)-free

#### Note

• To order the optional hardware go to <a href="https://www.vishay.com/doc?95172">www.vishay.com/doc?95172</a>

### **CIRCUIT CONFIGURATION**



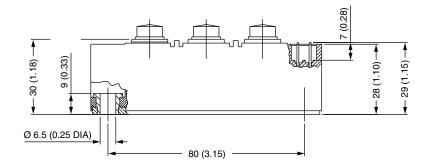
| LINKS TO RELATED DOCUMENTS |                          |  |  |  |
|----------------------------|--------------------------|--|--|--|
| Dimensions                 | www.vishay.com/doc?95067 |  |  |  |

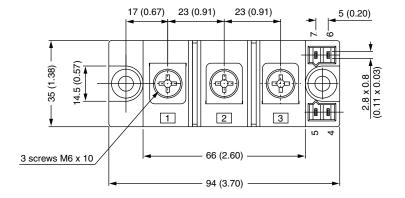


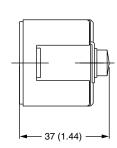
Vishay Semiconductors

### **INT-A-PAK IGBT/Thyristor**

### **DIMENSIONS** in millimeters (inches)











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